Current-Shunt Monitor, Voltage Output, Bi-Directional Zero-Drift

The NCS199A1, NCS199A2 and NCS199A3 are voltage output current shunt monitors that can measure voltage across shunts at common—mode voltages from -0.3 V to 26 V, independent of supply voltage. Three fixed gains are available: 50 V/V, 100 V/V or 200 V/V. The low offset of the zero—drift architecture enables current sensing with maximum drops across the shunt as low as 10 mV full—scale.

The devices can operate from a single +2.7 V to +26 V power supply, drawing a maximum of $100~\mu A$ of supply current. All versions are specified over the extended operating temperature range ($-40^{\circ}C$ to $+125^{\circ}C$).

Features

- Wide Common–Mode Input Range –0.3 V to 26 V
- Supply Voltage Range from 2.7 V to 26 V
- Low Offset Voltage ±150 μV Max
- Low Offset Drift (0.5 μV/°C)
- Low Gain Error (max 1.5%)
- Rail-to-rail Input and Output Capability
- Low Current Consumption (typ 65 μA, 100 μA max)
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-free Devices

Typical Applications

- Current Sensing (High-Side/Low-Side)
- Automotive
- Telecom
- Sensors



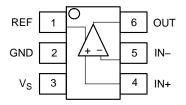
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www.onsemi.com



SC70-6 SQ SUFFIX CASE 419B

PIN CONNECTIONS



MARKING DIAGRAM



XXX = Specific Device Code (See page 4)

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

| Product | Gain | R3-R4 | R1-R2 |
|----------|------|-------|-------|
| NCS199A1 | 50 | 20 kΩ | 1 ΜΩ |
| NCS199A2 | 100 | 10 kΩ | 1 ΜΩ |
| NCS199A3 | 200 | 5 kΩ | 1 ΜΩ |

$$V_{OUT} = (I_{LOAD} \times R_{SHUNT})GAIN + V_{REF}$$

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 4 of this data sheet.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

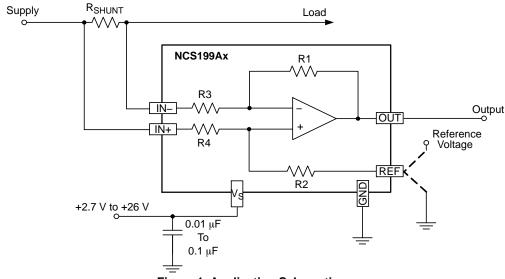


Figure 1. Application Schematic

Table 1. MAXIMUM RATINGS

| Rating Supply Voltage (Note 1) | | | Value | Unit |
|---|--|---------------------|-----------------------------------|------|
| | | | +26 | V |
| Analog Inputs | Differential (V _{IN+})-(V _{IN-}) | $V_{IN+,}V_{IN-}$ | -26 to +26 | V |
| | Common-Mode (Note 2) | | GND-0.3 to +26 | |
| REF Input | | V_{REF} | GND-0.3 to (V _s) +0.3 | V |
| Output (Note 2) | | V _{OUT} | GND-0.3 to (V _s) +0.3 | V |
| Input Current into Any Pin (Note 2) | | | 5 | mA |
| Maximum Junction Temperature | | T _{J(max)} | +150 | °C |
| Storage Temperature Range | | TSTG | -65 to +150 | °C |
| ESD Capability, Human Body Model (Note 3) | | HBM | ±3000 | V |
| ESD Capability, Machine Model (No | te 3) | MM | ±100 | V |
| Charged Device Model (Note 3) | | CDM | ±1000 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHĂRACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe operating parameters.
- 2. Input voltage at any pin may exceed the voltage shown if current at that pin is limited to 5 mA.
- 3. This device series incorporates ESD protection and is tested by the following methods
 - ESD Human Body Model tested per AEC-Q100-002 (EIA/JESD22-A114)
 - ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)
 - ESD Charged Device Model tested per AEC-Q100-011.
 - Latchup Current Maximum Rating: 50 mA per JEDEC standard: JESD78

Table 2. THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|---|----------------|-------|------|
| Thermal Characteristics, SC70 (Note 4) Thermal Resistance, Junction-to-Air (Note 5) | $R_{	heta JA}$ | 250 | °C/W |

- Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for safe
 operating parameters.
- Values based on copper area of 645 mm² (or 1 in²) of 1 oz copper thickness and FR4 PCB substrate.

Table 3. RECOMMENDED OPERATING RANGES

| Rating | Symbol | Min | Max | Unit |
|---------------------|----------------|-----|-----|------|
| Supply Voltage | V_S | 2.7 | 26 | V |
| Ambient Temperature | T _A | -40 | 125 | °C |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 4. ELECTRICAL CHARACTERISTICS Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C, guaranteed by characterization and/or design. At $T_A = +25^{\circ}C$, $V_{SENSE} = V_{IN+} - V_{IN-}$, $V_S = +5$ V, $V_{IN+} = 12$ V, and $V_{REF} = V_S/2$, unless otherwise noted.

| | ameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------------|-------------------------------|---|-----------------|------|------------------|--------------|--------|
| GAIN | | | | | | | |
| NCS199A1 NCS199A2 NCS199A3 | | | G | | 50 100 200 | | V/V |
| Gain Error | | $V_{SENSE} = -5 \text{ mV to } 5 \text{ mV}$ | G _e | | ±0.2 | ±1.5 | % |
| Gain Error vs. Tem | perature | $T_A = -10^{\circ}C \text{ to } 125^{\circ}C$ | | | 7 | 20 | ppm/°C |
| Nonlinearity Error | | $V_{SENSE} = -5 \text{ mV to } 5 \text{ mV}$ | | | ±0.01 | | % |
| Maximum Capaciti | ve Load | No sustained oscillation | | | 1 | | nF |
| VOLTAGE OFFSE | т | | | | | | |
| Offset Voltage | NCS199A1/2/3 NCV199A2 | (RTI Note 6), V _{SENSE} = 0 mV | V _{OS} | | ±5.0 ±20 | ±150 ±200 | μV |
| Offset Drift N | CS199A2, NCS199A3 NCS199A1 | | δV/δΤ | | 0.1 0.5 | 0.6 2.0 | μV/°C |
| INPUT | | | - | | • | | |
| Input Bias Current | | V _{SENSE} = 0 mV | I _{IB} | | | 60 | μΑ |
| Common-Mode In | put Voltage Range | | V_{CM} | -0.3 | | 26 | V |
| Common–Mode Rejection Ratio | NCS199A2, NCS199A3 | $V_S = 5 \text{ V}, V_{IN+} = 2 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV}$ | CMRR | 100 | 115 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 3 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV}$ | | 100 | 115 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 0 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV } (T_A = -10^{\circ}\text{C to } 85^{\circ}\text{C})$ | | 100 | 120 | | dB |
| Common–Mode Rejection Ratio | NCS199A1 | $V_S = 5 \text{ V}, V_{IN+} = 2 \text{ V to } +26 \text{ V}, V_{SENSE} = 0 \text{ mV}$ | CMRR | 97 | 110 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 3 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV}$ | | 97 | 110 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 0 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV } (T_A = -10^{\circ}\text{C to } 85^{\circ}\text{C})$ | | 97 | 115 | | dB |
| Common–Mode Rejection Ratio | NCV199A2 | $V_S = 5 \text{ V}, V_{IN+} = 2 \text{ V to } +26 \text{ V}, V_{SENSE} = 0 \text{ mV}$ | CMRR | 95 | 115 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 3 \text{ V to } +26 \text{ V}, \\ V_{SENSE} = 0 \text{ mV}$ | | 95 | 115 | | dB |
| | | $V_S = 3.3 \text{ V}, V_{IN+} = 0 \text{ V to +26 V}, \\ V_{SENSE} = 0 \text{ mV } (T_A = -10^{\circ}\text{C to }85^{\circ}\text{C})$ | | 95 | 120 | | dB |
| OUTPUT | | | | | | | |
| Output Voltage Low | | Referenced from GND $R_L = 10 \text{ k}\Omega$ to Ground | V _{OL} | | 5 | 50 | mV |
| Output Voltage High | | Referenced from V_S $R_L = 10 \text{ k}\Omega$ to Ground | V _{OH} | | 0.05 | 0.2 | V |
| DYNAMIC PERFO | RMANCE | | | | | | |
| Bandwidth (f _{-3dB}) | | C_{LOAD} = 10 pF, NCS199A1 C_{LOAD} = 10 pF, NCS199A2 C_{LOAD} = 10 pF, NCS199A3 | BW | | 100 60 40 | | kHz |
| Slew Rate | | SLOAD 13 P., 1100 100.10 | SR | | 0.4 | | V/µs |
| NOISE | | <u> </u> | Ü. | | Ų.Ŧ | 1 | ν/μο |
| Spectral Density, 1 | kHz (RTI Note 6) | | e _n | | 35 | | nV/√Hz |
| | , | ed in the Electrical Characteristics for the | | | | | 1 |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 6. RTI = referenced-to-input.

Table 4. ELECTRICAL CHARACTERISTICS Boldface limits apply over the specified temperature range, $T_A = -40^{\circ}C$ to 125°C, guaranteed by characterization and/or design. At $T_A = +25^{\circ}C$, $V_{SENSE} = V_{IN+} - V_{IN-}$, $V_S = +5$ V, $V_{IN+} = 12$ V, and $V_{REF} = V_S/2$, unless otherwise noted.

| Parameter | Test Conditions | Symbol | Min | Тур | Max | Unit |
|------------------------------------|--|-----------------|-----|------|-----|------|
| POWER SUPPLY | | | | | | |
| Operating Voltage Range | V _{SENSE} = 0 mV | Vs | 2.7 | | 26 | V |
| Quiescent Current | V _{SENSE} = 0 mV | I _{DD} | | 65 | 100 | μΑ |
| Quiescent Current over Temperature | V _{SENSE} = 0 mV | | | | 115 | μΑ |
| Power Supply Rejection Ratio | V_S = +2.7 V to +26 V, V_{IN+} =18 V, V_{SENSE} = 0 mV | PSRR | | ±0.1 | ±10 | μV/V |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 6. RTI = referenced-to-input.

ORDERING INFORMATION

| Device | Gain | Marking | Package | Shipping [†] |
|-----------------------------------|------|---------|---------------------|-----------------------|
| NCS199A1SQT2G | 50 | ACQ | | |
| NCS199A2SQT2G | 100 | ACR | | |
| NCS199A3SQT2G | 200 | ACP | SC70-6 (Pb-Free) | 3000 / Tape and Reel |
| NCV199A2SQT2G* (In Development)** | 100 | TBD | (1.2.1.00) | |
| NCV199A3SQT2G* (In Development)** | 200 | TBD |] | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

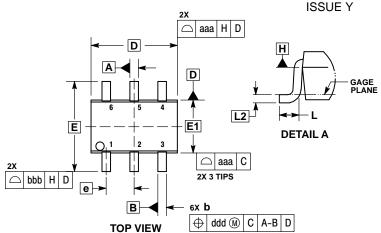
^{*}NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

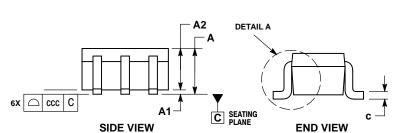
^{**} Contact local sales office for availability.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02



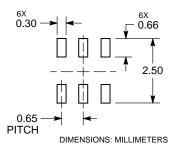


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH. PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
- THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| | MIL | LIMETE | ERS | | INCHES | 3 |
|-----|------------|---------|------|-------|----------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | - | | 1.10 | | | 0.043 |
| A1 | 0.00 | | 0.10 | 0.000 | | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| С | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| е | | 0.65 BS | С | 0 | .026 BS | С |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | | 0.15 BS | C | | 0.006 BS | SC |
| aaa | 0.15 0.006 | | | | | |
| bbb | | 0.30 | | | 0.012 | |
| ccc | 0.10 | | | | 0.004 | |
| ddd | 0.10 0.004 | | | | | |

RECOMMENDED SOLDERING FOOTPRINT



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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